SiO2 Films, Grown using Unaxis ICP Tool (PM3) as well as PECVD Tool, Characterizations			
	100 ^{o}C (ICP)	250 ^{o}C (ICP)	250 ^{o}C (PECVD)
Refractive Index	1.47	1.49	1.46
Deposition Rate (nm/min.)	33.6	31.9	~40
Buffered HF Etch Rate (nm/min.)	242	196	~712
Stress (~20nm thick SiO_2 Film on a Si Wafer) (MPa)	-332	-275	−307